

Abstract

A method of manufacturing a semiconductor device comprises steps of: forming a first metal film having a reducing property on a semiconductor substrate; thermal treating the resulting semiconductor substrate for reducing a native oxide film naturally formed on the semiconductor substrate and for forming a first silicide film on the semiconductor substrate; removing an unreacted first metal film selectively; forming a second metal film on the semiconductor substrate; and thermal treating the resulting semiconductor substrate for forming a second silicide film on a surface of the semiconductor substrate which includes a region where the first silicide film is formed.

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